

Silicon NPN Power Transistors

2SC4369

DESCRIPTION

- With TO-220F package
- Complement to type 2SA1658
- Good linearity of h_{FE}

APPLICATIONS

- For general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

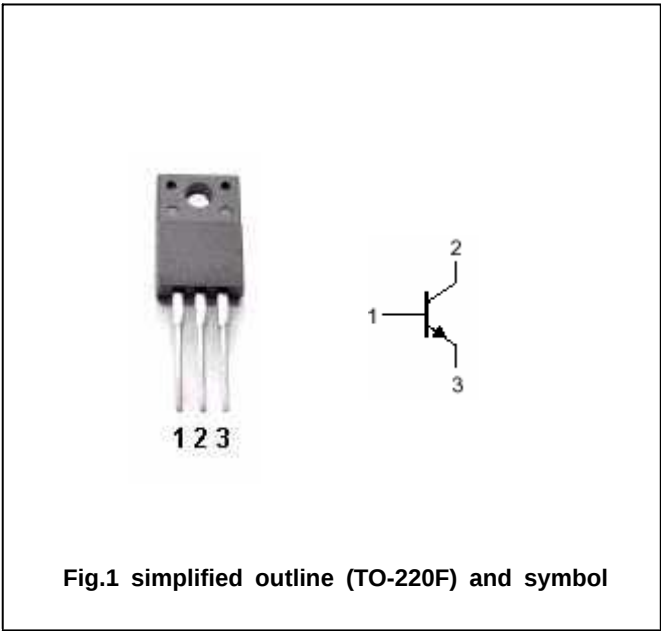


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	30	V
V_{CEO}	Collector-emitter voltage	Open base	30	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
I_B	Base current		0.3	A
P_C	Collector dissipation	$T_C=25$	15	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $I_B=0$	30			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A$; $I_B=0.2A$			0.8	V
V_{BE}	Base-emitter on voltage	$I_C=0.5A$; $V_{CE}=2V$			1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=20V$; $I_E=0$			1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			1.0	μA
h_{FE-1}	DC current gain	$I_C=0.5A$; $V_{CE}=2V$	70		240	
h_{FE-2}	DC current gain	$I_C=2.5A$; $V_{CE}=2V$	25			
f_T	Transition frequency	$I_C=0.5A$; $V_{CE}=2V$		100		MHz

◆ h_{FE-1} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

